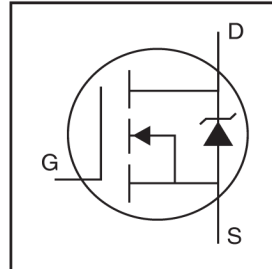


IRLR/U2703PbF

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Ultra Low On-Resistance
- Surface Mount (IRLR2703)
- Straight Lead (IRLU2703)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

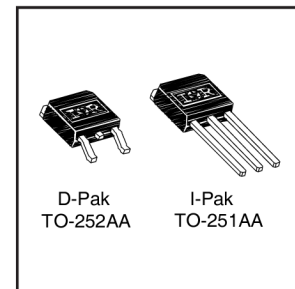


$V_{DSS} = 30V$
$R_{DS(on)} = 0.045\Omega$
$I_D = 23A$ ⑤

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	23 ⑤	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	16	
I_{DM}	Pulsed Drain Current ①	96	
$P_D @ T_C = 25^\circ C$	Power Dissipation	45	W
	Linear Derating Factor	0.30	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy ②	77	mJ
I_{AR}	Avalanche Current ①	14	A
E_{AR}	Repetitive Avalanche Energy ①	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

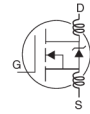
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	3.3	°C/W
$R_{\theta JA}$	Case-to-Ambient (PCB mount)**	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

** When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.030	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.045	Ω	V _{GS} = 10V, I _D = 14A ④
		—	—	0.065		V _{GS} = 4.5V, I _D = 12A ④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	6.4	—	—	S	V _{DS} = 25V, I _D = 14A ⑦
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 30V, V _{GS} = 0V
		—	—	250		V _{DS} = 24V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -16V
Q _g	Total Gate Charge	—	—	15	nC	I _D = 14A
Q _{gs}	Gate-to-Source Charge	—	—	4.6		V _{DS} = 24V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	9.3		V _{GS} = 4.5V, See Fig. 6 and 13 ④ ⑦
t _{d(on)}	Turn-On Delay Time	—	8.5	—	ns	V _{DD} = 15V
t _r	Rise Time	—	140	—		I _D = 14A
t _{d(off)}	Turn-Off Delay Time	—	12	—		R _G = 12Ω, V _{GS} = 4.5V
t _f	Fall Time	—	20	—		R _D = 1.0Ω, See Fig. 10 ④ ⑦
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑥
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	450	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	210	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	110	—		f = 1.0MHz, See Fig. 5 ⑦



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	23 ⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	96		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 14A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	65	97	ns	T _J = 25°C, I _F = 14A
Q _{rr}	Reverse Recovery Charge	—	140	210	nC	di/dt = 100A/μs ④ ⑦
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V_{DD} = 15V, starting T_J = 25°C, L = 570μH
R_G = 25Ω, I_{AS} = 14A. (See Figure 12)
- ③ I_{SD} ≤ 14A, di/dt ≤ 140A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

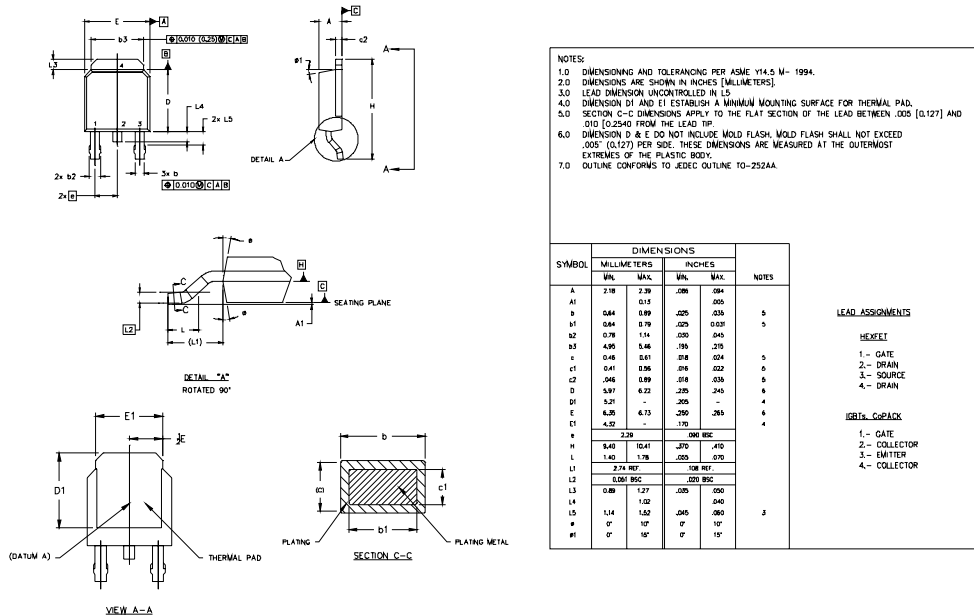
- ⑤ Calculated continuous current based on maximum allowable junction temperature; Package limitation current = 20A.
- ⑥ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact.
- ⑦ Uses IRL2703 data and test conditions.

IRLR/U2703PbF

International
IR Rectifier

D-Pak (TO-252AA) Package Outline

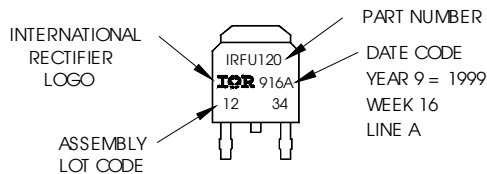
Dimensions are shown in millimeters (inches)



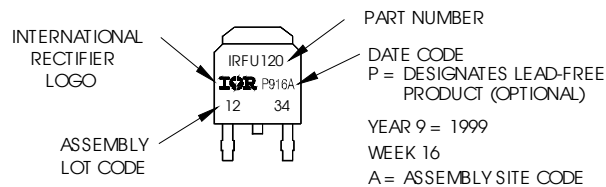
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON VW 16, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

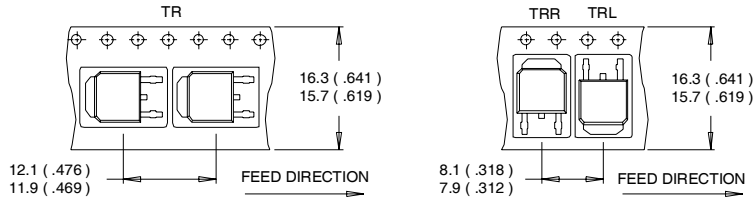


OR

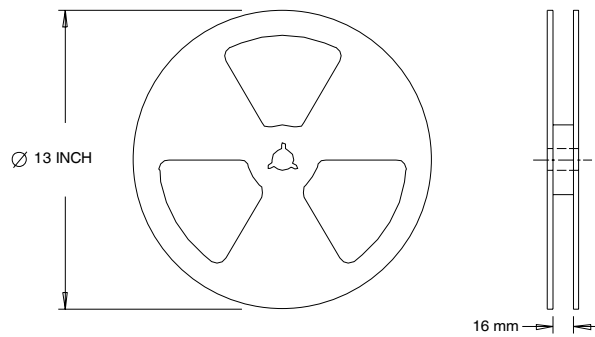


D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.